

Features

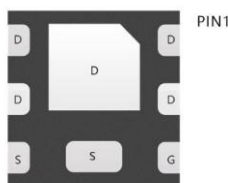
- Leading trench technology for low $R_{DS(on)}$
- Low Gate Charge

Product Summary

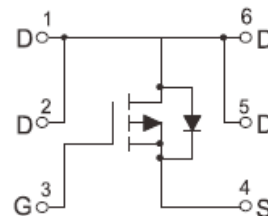
V_{DS}	$R_{DS(on)}$ TYP	I_D
-12V	30mΩ@-4.5V	-6A

Application

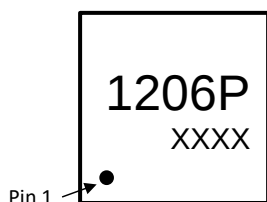
- Video monitor
- Power management



DFN2X2-6L view



Schematic diagram



1206P: Device code
 XXXX: Code
 Solid dot: Pin1 indicator

Marking and pin assignment



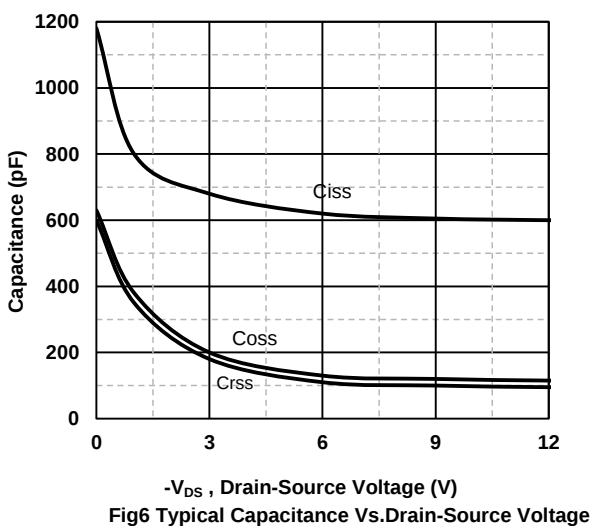
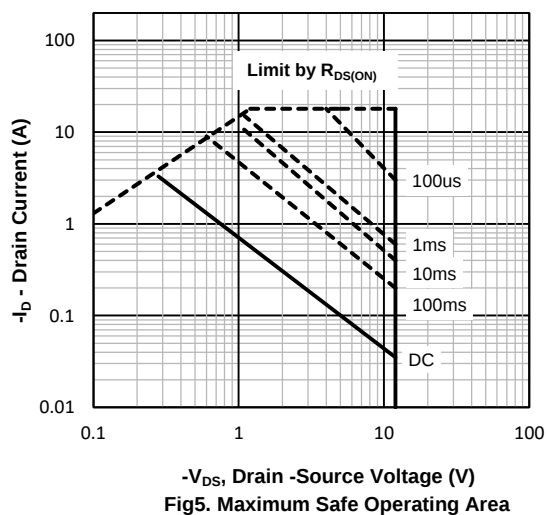
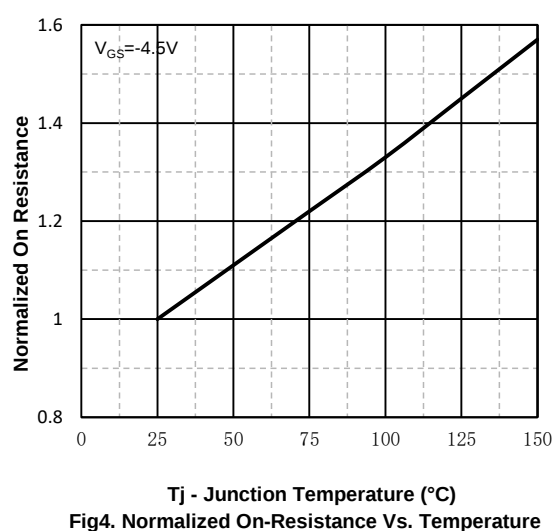
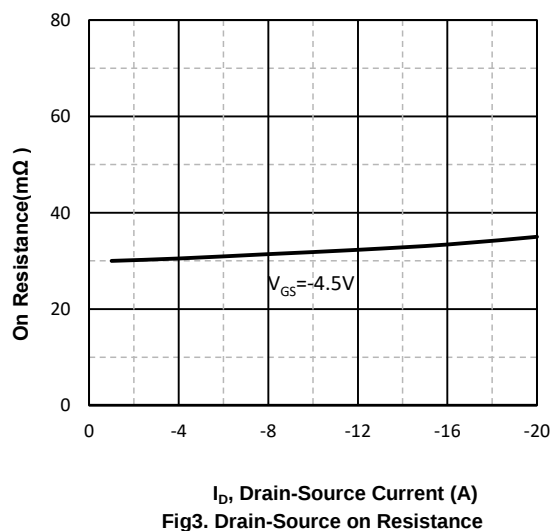
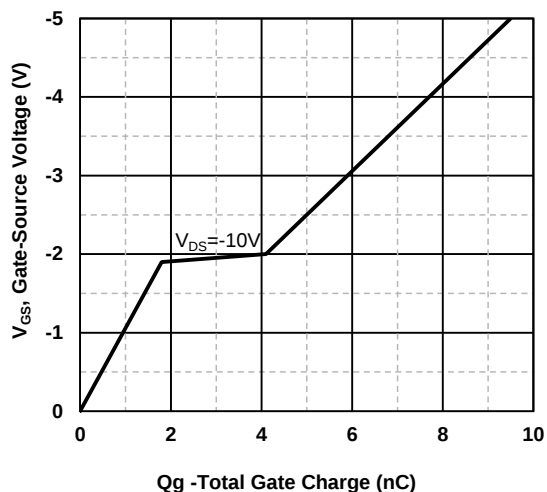
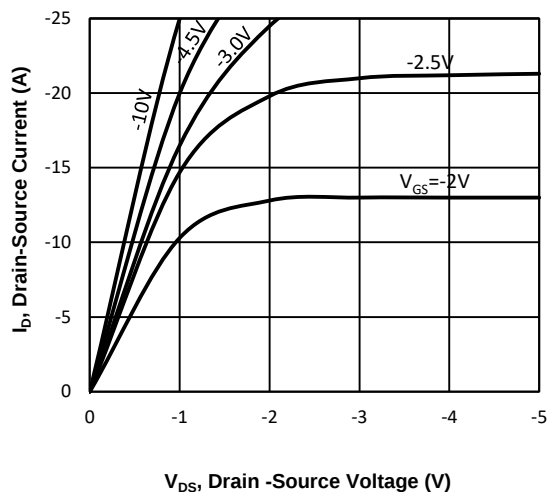
Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)				
Symbol	Parameter		Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)				
V _{DS}	Drain-Source Breakdown Voltage		-12	V
V _{GS}	Gate-Source Voltage		±8	V
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	°C
I _S	Diode Continuous Forward Current	Tc=25°C	-6	A
Mounted on Large Heat Sink				
I _{DM}	Pulse Drain Current Tested	Tc=25°C	-18	A
I _D	Continuous Drain Current	Tc=25°C	-6	A
P _D	Maximum Power Dissipation	Tc=25°C	2.1	W
R _{θJA}	Thermal Resistance Junction-to-Ambient		165	°C/W

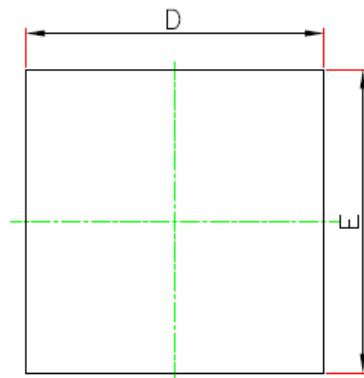
Ordering Information (Example)						
Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLSM1206P	DFN2X2-6L	1206P	3,000	45,000	180,000	7"reel

Electrical Characteristics (T _J =25℃ unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T _J = 25℃ (unless otherwise stated)						
B _{V(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-12	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-12V, V _{GS} =0V	--	--	-1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±8V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-0.45	-0.6	-1.0	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =-4.5V, I _D =-6A	--	30	45	mΩ
Dynamic Electrical Characteristics @ T _J = 25℃ (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =-10V, V _{GS} =0V, f=1MHz	--	606	--	pF
C _{OSS}	Output Capacitance		--	114	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	103	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =-10V, I _D =-6A, V _{GS} =-10V	--	8.48	--	nC
Q _{gs}	Gate Source Charge		--	1.54	--	nC
Q _{gd}	Gate Drain Charge		--	2.61	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =-10V, I _D =-6A, V _{GS} =-4.5V, R _G =3Ω	--	5.8	--	nS
t _r	Turn-on Rise Time		--	34.8	--	nS
t _{d(off)}	Turn-Off Delay Time		--	51.4	--	nS
t _f	Turn-Off Fall Time		--	52	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _J =25℃, I _S =-6A	--	--	-1.2	V

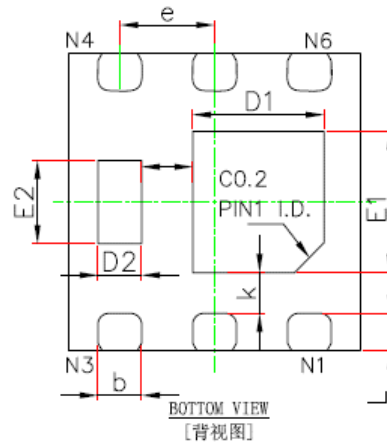
Typical Operating Characteristics



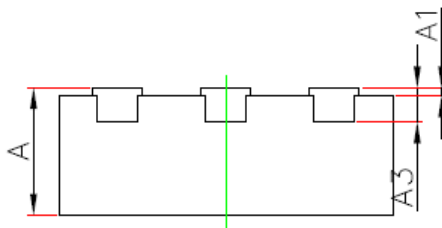
DFN2X2-6L Package information



TOP VIEW
[顶视图]



BOTTOM VIEW
[背视图]



SIDE VIEW
[侧视图]

Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.600	0.700	0.023	0.027
A1	0.000	0.050	0.000	0.001
A3	0.203REF		0.007REF	
b	0.315	0.415	0.012	0.016
D	1.924	2.076	0.075	0.081
E	1.924	2.076	0.075	0.081
e	0.650TYP		0.225TYP	
L	0.224	0.376	0.008	0.014
k	0.200	-	0.007	-
E1	1.000	1.200	0.039	0.047
D1	0.900	1.100	0.035	0.043
E2	0.700	0.900	0.027	0.035
D2	0.150	0.350	0.005	0.013